

Accepted Manuscript

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PII: S0040-6090(17)30230-4
DOI: doi: [10.1016/j.tsf.2017.03.045](https://doi.org/10.1016/j.tsf.2017.03.045)
Reference: TSF 35893
To appear in: *Thin Solid Films*
Received date: 28 February 2016
Revised date: 18 March 2017
Accepted date: 22 March 2017

Please cite this article as: Ruiqin Peng, Shujie Jiao, Dongwei Jiang, Hongtao Li, Liancheng Zhao, Dark current mechanisms and spectral response of SiO₂-passivated photodiodes based on InAs/GaSb superlattice. The address for the corresponding author was captured as affiliation for all authors. Please check if appropriate. Tsf(2017), doi: [10.1016/j.tsf.2017.03.045](https://doi.org/10.1016/j.tsf.2017.03.045)

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Dark current mechanisms and spectral response of SiO₂-passivated photodiodes based on InAs/GaSb superlattice

Ruiqin Peng^a, Shujie Jiao^{a*}, Dongwei Jiang^a, Hongtao Li^a, Liancheng Zhao^a

^aSchool of Materials Science and Engineering, Harbin Institute of Technology, Harbin 150001, P. R. China

ABSTRACT

The electrical performance of SiO₂ passivated type-II superlattice double heterostructure photodiodes is demonstrated. Compared to unpassivated samples, a dark current of 4.009×10^{-5} A/cm² and the corresponding differential resistance-area of 165.82 Ω.cm² at zero bias voltage are achieved at 77 K. The temperature-dependence and bias-dependence of the dark current are studied experimentally. According to fitting results, the existence of the SiO₂ passivated layer alters the band bending at the interface, which influence the generation-recombination and trap-assisted tunneling current and then it present that the total dark current is reduced by introducing the SiO₂ passivation technology. At 77 K, the corresponding spectral responsivity and detectivity of the samples are measured at a bias voltage of -50 mV and the 100% cutoff wavelength is determined to be 10.6 μm, which is fitted well with the simulation results of temperature dependence of experimental data.

Keywords: InAs/GaSb; Passivation; Dark current; Mechanism.

*Corresponding author. Shujie Jiao, Tel.: +86 451 86417763; E-mail: shujiejiao@gmail.com.

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